

NCE30D2519-VB Datasheet

N- and P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY				
	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
N-Channel	30	0.007 at V _{GS} = 10 V	65	6 nC
		0.010 at V _{GS} = 4.5 V	50	
P-Channel	- 30	0.025 at V _{GS} = - 10 V	- 35	8 nC
		0.035 at V _{GS} = - 4.5 V	- 25	

FEATURES

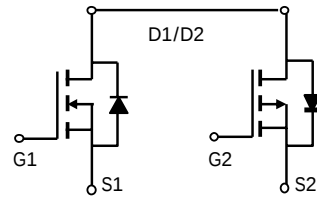
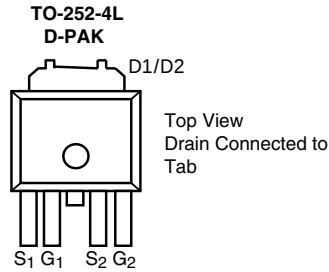
- Halogen-free According to IEC 61249-2-21 Available
- Trench Power MOSFET
- 100 % R_g and UIS Tested

APPLICATIONS

- CCFL Inverter



RoHS
COMPLIANT
HALOGEN
FREE
Available



N-channel

P-channel

ABSOLUTE MAXIMUM RATINGS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted					
Parameter		Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage		V_{DS}	30	- 30	V
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current ($T_J = 150\text{ }^{\circ}\text{C}$)	$T_C = 25\text{ }^{\circ}\text{C}$	I_D	65	- 35	A
	$T_C = 70\text{ }^{\circ}\text{C}$		45	- 25	
	$T_A = 25\text{ }^{\circ}\text{C}$		20 ^{b, c}	- 17 ^{b, c}	
	$T_A = 70\text{ }^{\circ}\text{C}$		14 ^{b, c}	- 12 ^{b, c}	
Pulsed Drain Current (10 μs Pulse Width)		I_{DM}	195	- 95	
Source Drain Current Diode Current	$T_C = 25\text{ }^{\circ}\text{C}$	I_S	2.6	- 2.8	
	$T_A = 25\text{ }^{\circ}\text{C}$		1.7 ^{b, c}	- 1.7 ^{b, c}	
Pulsed Source-Drain Current		I_{SM}	20	- 15	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	20	15	mJ
Single Pulse Avalanche Energy		E_{AS}	8.1	13	
Maximum Power Dissipation	$T_C = 25\text{ }^{\circ}\text{C}$	P_D	9.1	8.4	W
	$T_C = 70\text{ }^{\circ}\text{C}$		6	5	
	$T_A = 25\text{ }^{\circ}\text{C}$		2 ^{b, c}	2 ^{b, c}	
	$T_A = 70\text{ }^{\circ}\text{C}$		1.3 ^{b, c}	1.3 ^{b, c}	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	N-Channel		P-Channel		Unit
			Typ.	Max.	Typ.	Max.	
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 s	R _{thJA}	55	62.5	53	62.5	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	33	40	30	37	

Notes:

a. Based on T_C = 25 °C.

b. Surface Mounted on 1" x 1" FR4 board.

c. t = 10 s.

d. Maximum under Steady State conditions is 110 °C/W for N-Channel and P-Channel.

SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions		Min.	Typ. ^a	Max.	Unit
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	N-Ch	30			V
		V _{GS} = 0 V, I _D = - 250 μA	P-Ch	- 30			
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA	N-Ch		55		mV
		I _D = - 250 μA	P-Ch		- 50		
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J	I _D = 250 μA	N-Ch		- 6		
		I _D = - 250 μA	P-Ch		4		
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	N-Ch	1		3	V
		V _{DS} = V _{GS} , I _D = - 250 μA	P-Ch	- 1		- 3	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	N-Ch			100	nA
			P-Ch			- 100	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	N-Ch			1	μA
		V _{DS} = - 30 V, V _{GS} = 0 V	P-Ch			- 1	
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C	N-Ch			10	
		V _{DS} = - 30 V, V _{GS} = 0 V, T _J = 55 °C	P-Ch			- 10	
On-State Drain Current ^b	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	N-Ch	20			A
		V _{DS} ≤ - 5 V, V _{GS} = - 10 V	P-Ch	- 25			
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 7 A	N-Ch		0.007		Ω
		V _{GS} = - 10 V, I _D = - 6 A	P-Ch		0.025		
		V _{GS} = 4.5 V, I _D = 6 A	N-Ch		0.010		
		V _{GS} = - 4.5 V, I _D = - 5 A	P-Ch		0.035		
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 7 A	N-Ch		15		S
		V _{DS} = - 15 V, I _D = - 6 A	P-Ch		8.5		
Dynamic ^a							
Input Capacitance	C _{iss}	N-Channel V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	N-Ch		625		pF
			P-Ch		950		
Output Capacitance	C _{oss}	P-Channel V _{DS} = - 15 V, V _{GS} = 0 V, f = 1 MHz	N-Ch		65		
			P-Ch		85		
Reverse Transfer Capacitance	C _{rss}		N-Ch		40		
			P-Ch		60		
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 4.3 A	N-Ch		13	20	nC
		V _{DS} = - 15 V, V _{GS} = - 10 V, I _D = - 3.1 A	P-Ch		14.5	22	
	N-Channel V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 4.3 A	N-Ch		6	9		
		P-Ch		8	12		
Gate-Source Charge	Q _{gs}	P-Channel V _{DS} = - 15 V, V _{GS} = - 4.5 V, I _D = - 3.1 A	N-Ch		2.3		
	P-Ch			2.2			
Gate-Drain Charge	Q _{gd}		N-Ch		2.6		
			P-Ch		3.7		
Gate Resistance	R _g	f = 1 MHz	N-Ch		2	3	Ω
			P-Ch		14	20	

SPECIFICATIONS T _J = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions		Min.	Typ. ^a	Max.	Unit	
Dynamic ^a								
Turn-On Delay Time	t _{d(on)}	N-Channel V _{DD} = 30 V, R _L = 8.8 Ω I _D ≅ 3.4 A, V _{GEN} = 4.5 V, R _g = 1 Ω	N-Ch		15	25	ns	
			P-Ch		30	45		
Rise Time	t _r		N-Ch		65	100		
			P-Ch		70	105		
Turn-Off Delay Time	t _{d(off)}	P-Channel V _{DD} = - 30 V, R _L = 12.5 Ω I _D ≅ - 2.4 A, V _{GEN} = - 4.5 V, R _g = 1 Ω	N-Ch		15	25		
			P-Ch		40	60		
Fall Time	t _f		N-Ch		10	15		
			P-Ch		30	45		
Turn-On Delay Time	t _{d(on)}	N-Channel V _{DD} = 30 V, R _L = 8.8 Ω I _D ≅ 3.4 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch		10	15		
			P-Ch		10	15		
Rise Time	t _r		N-Ch		15	25		
			P-Ch		13	20		
Turn-Off Delay Time	t _{d(off)}	P-Channel V _{DD} = - 30 V, R _L = 12.5 Ω I _D ≅ - 2.4 A, V _{GEN} = - 10 V, R _g = 1 Ω	N-Ch		20	30		
			P-Ch		35	55		
Fall Time	t _f		N-Ch		10	15		
			P-Ch		30	45		
Drain-Source Body Diode Characteristics								
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	N-Ch			2.6	A	
			P-Ch			- 2.8		
Pulse Diode Forward Current ^a	I _{SM}		N-Ch			20		
			P-Ch			- 25		
Body Diode Voltage	V _{SD}	I _S = 1.7 A	N-Ch		0.8	1.2	V	
		I _S = - 2 A	P-Ch		- 0.8	- 1.2		
Body Diode Reverse Recovery Time	t _{rr}	N-Channel I _F = 1.7 A, dI/dt = 100 A/μs, T _J = 25 °C	N-Ch		30	60	ns	
			P-Ch		30	50		
Body Diode Reverse Recovery Charge	Q _{rr}		P-Channel I _F = - 2 A, dI/dt = - 100 A/μs, T _J = 25 °C	N-Ch		32	50	nC
				P-Ch		35	60	
Reverse Recovery Fall Time	t _a			N-Ch		25		ns
				P-Ch		16		
Reverse Recovery Rise Time	t _b		N-Ch		5			
			P-Ch		14			

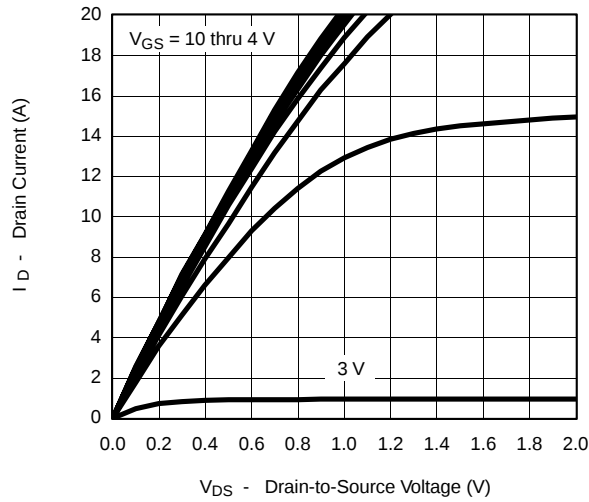
Notes:

a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

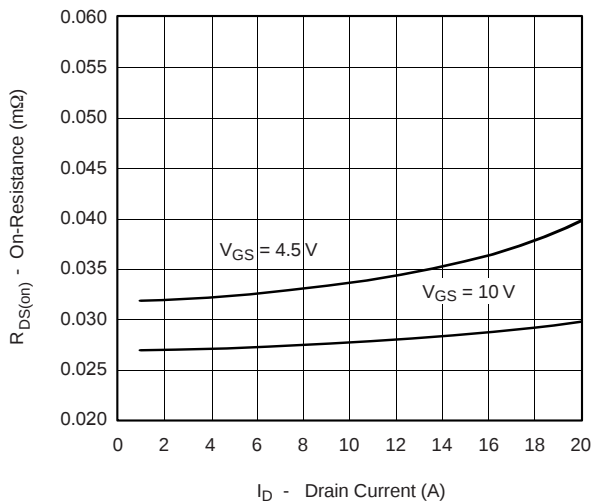
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



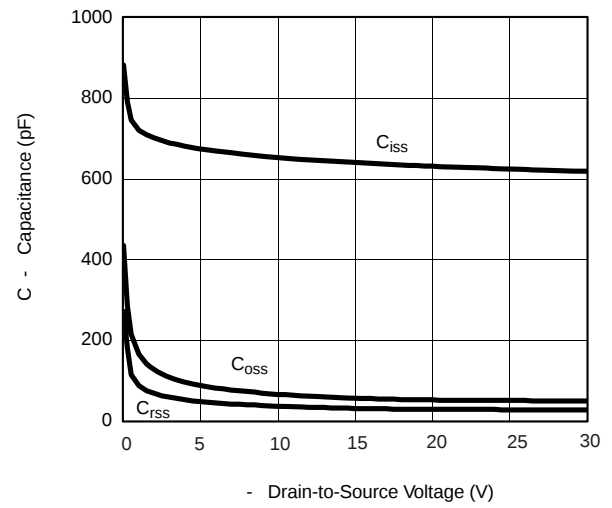
Output Characteristics



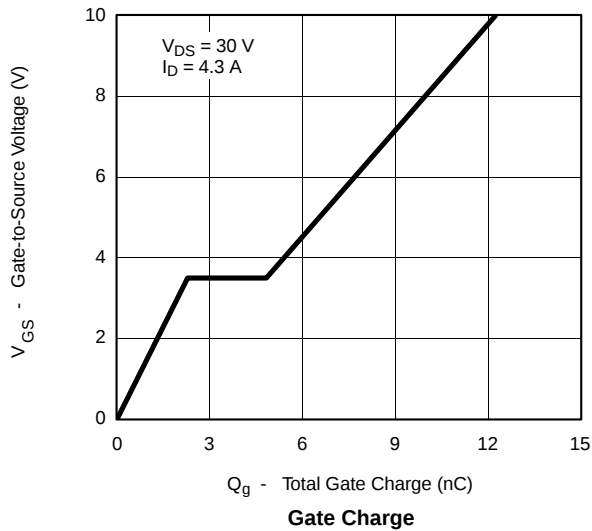
Transfer Characteristics



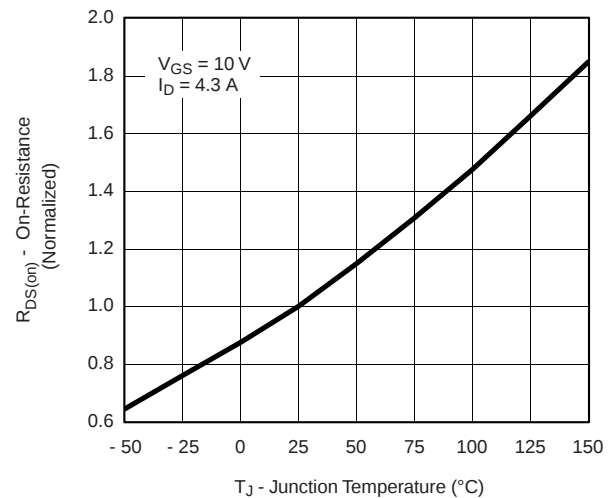
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

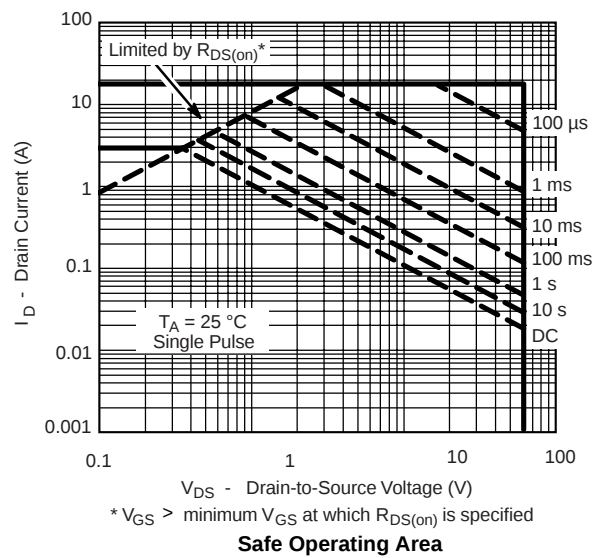
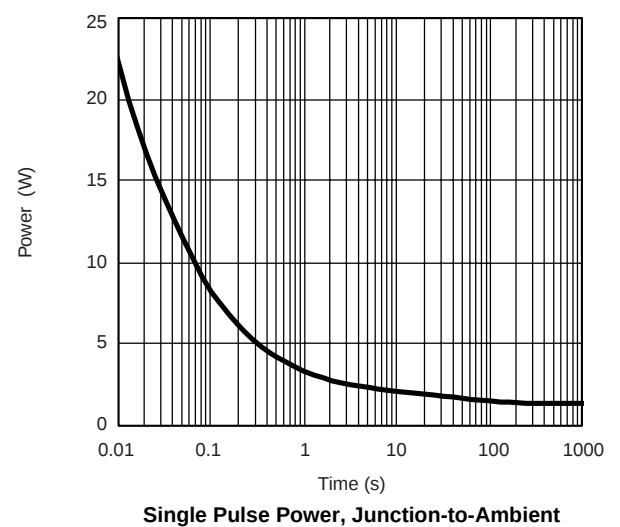
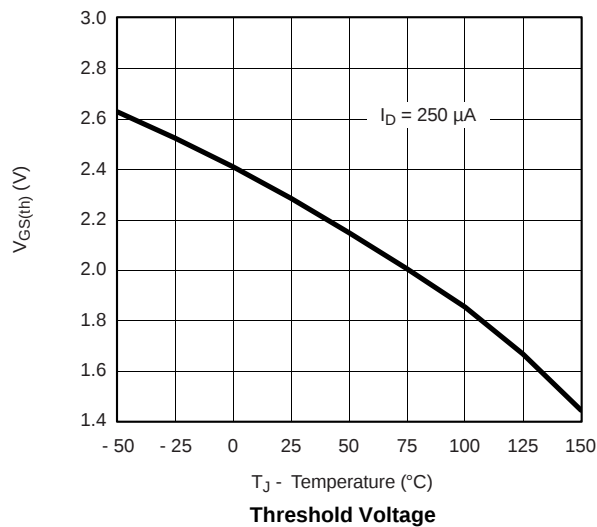
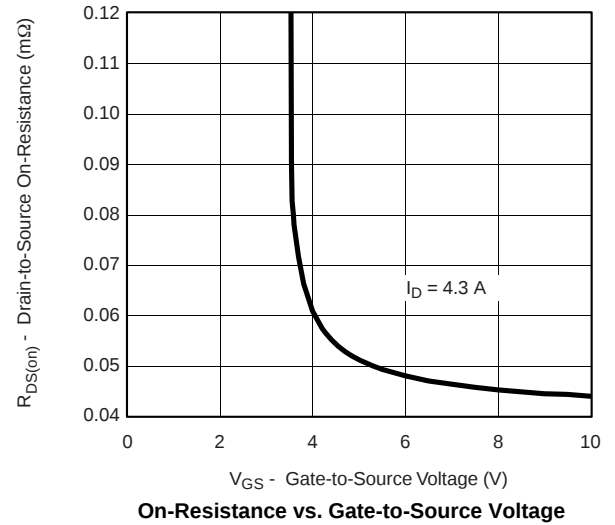
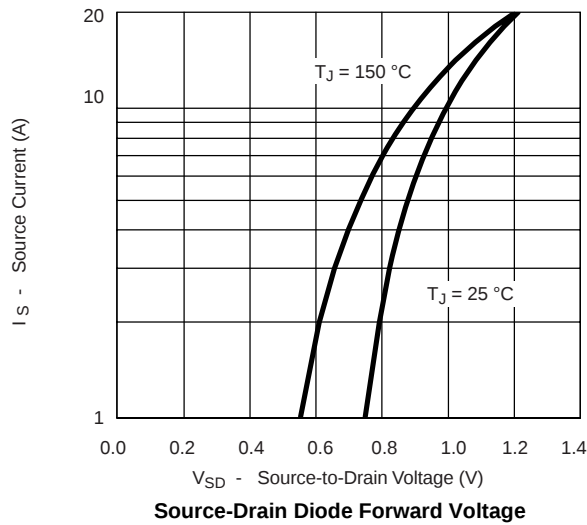


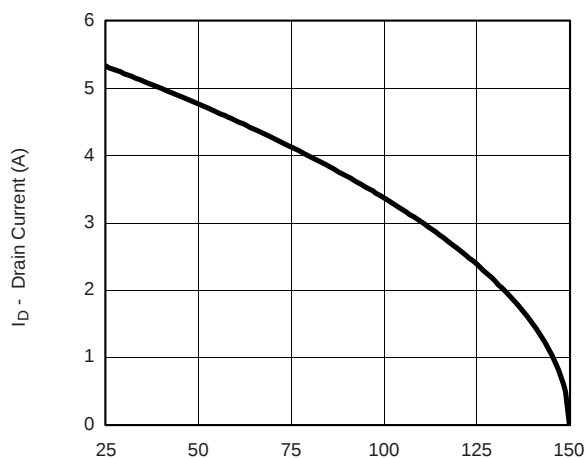
Gate Charge

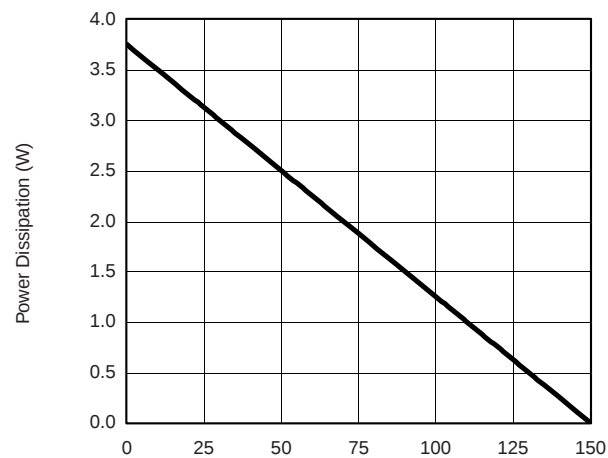


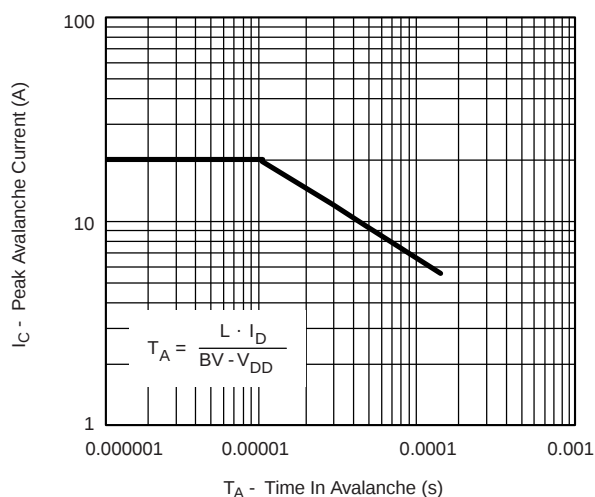
On-Resistance vs. Junction Temperature

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

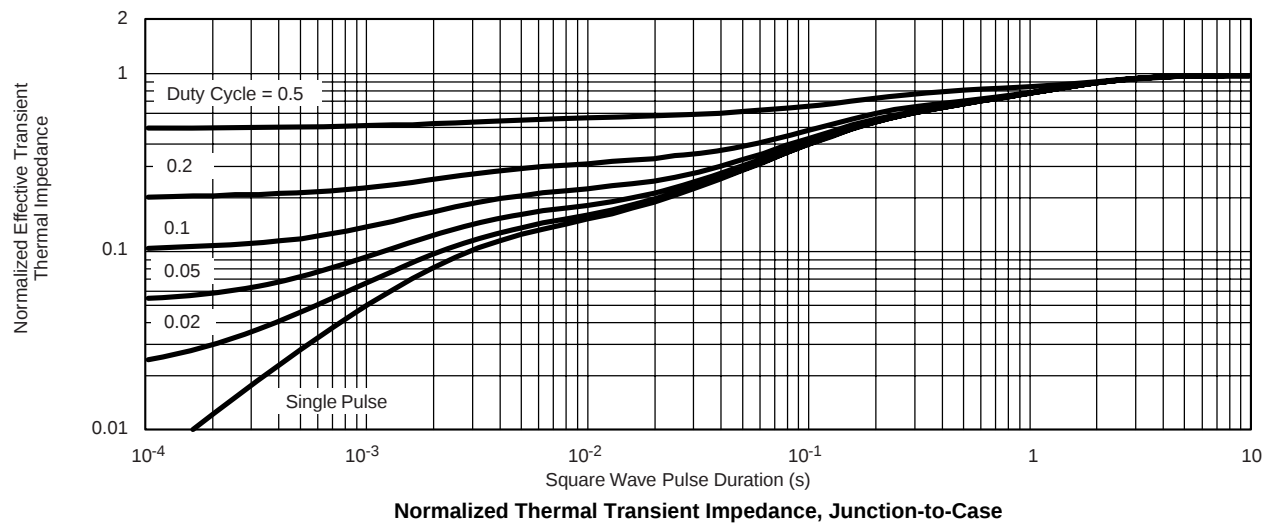
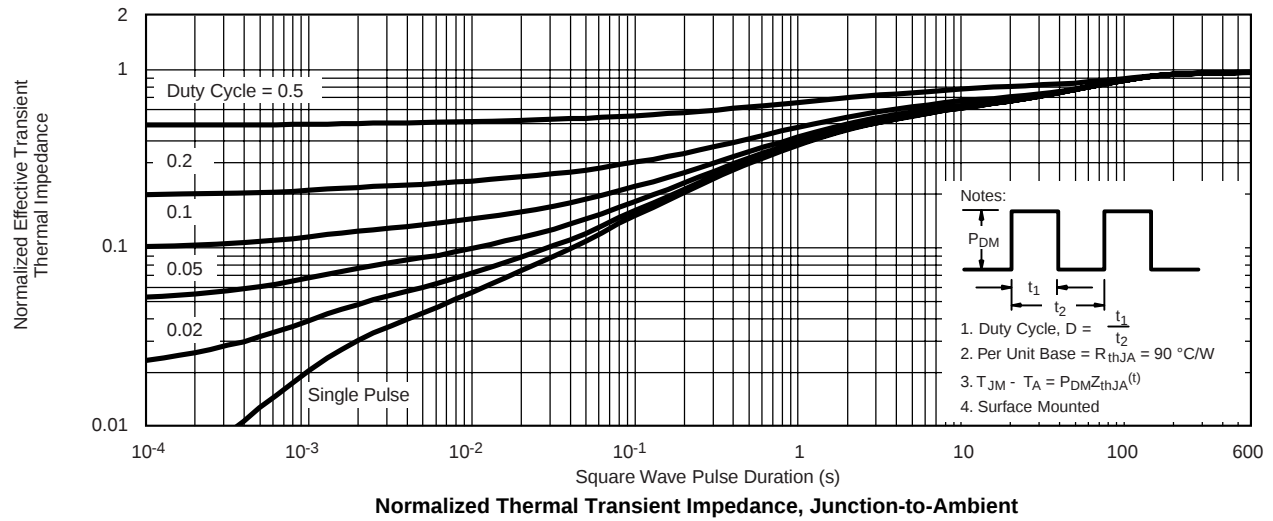


N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

 T_C - Case Temperature (°C)

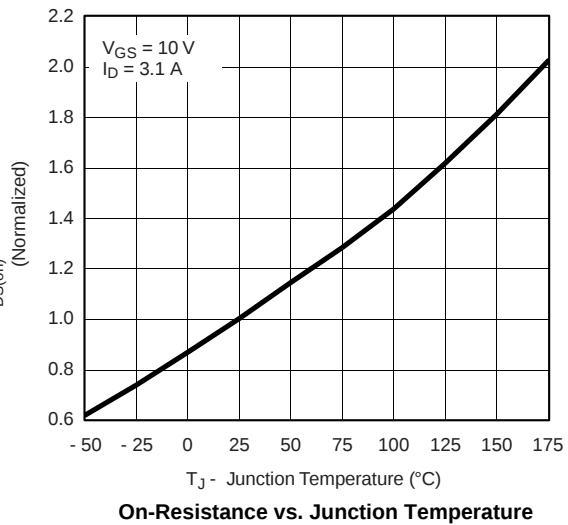
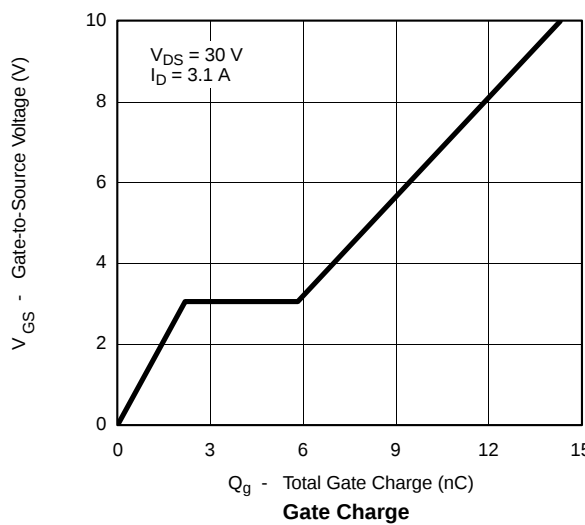
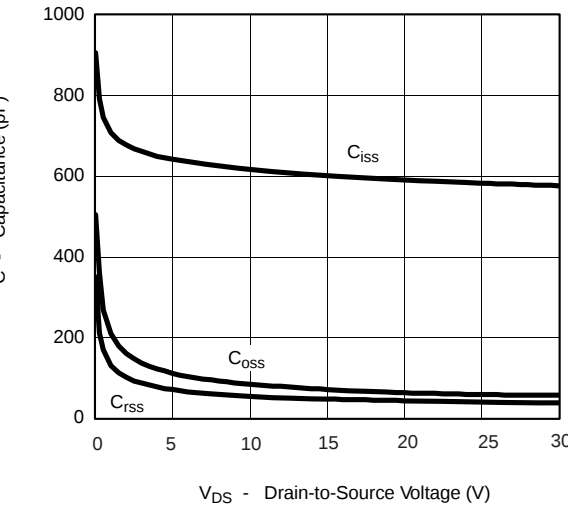
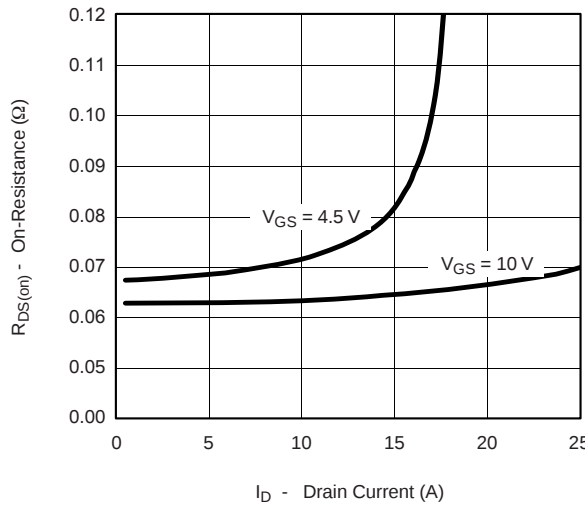
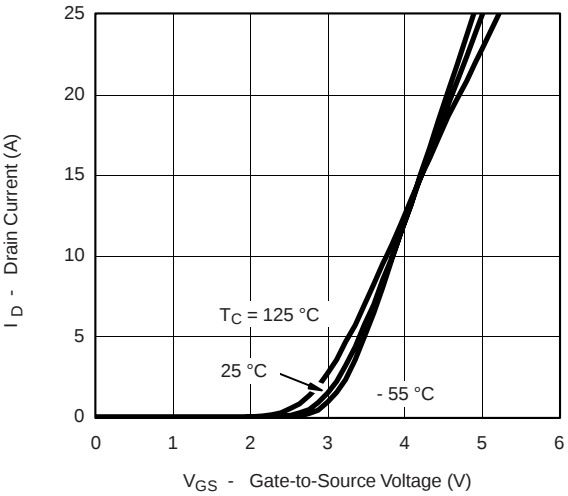
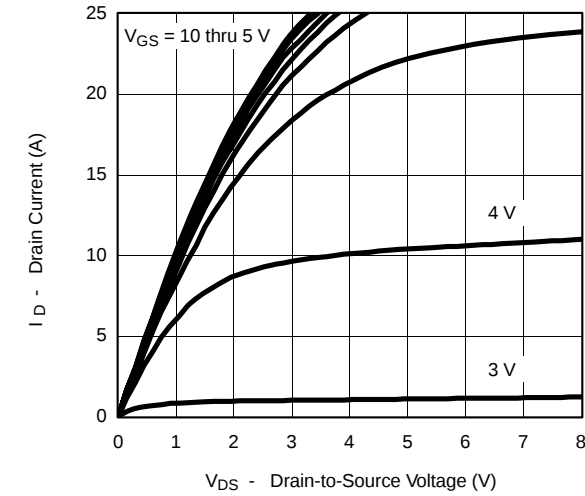
Current Derating*

 T_C - Case Temperature (°C)

Power Derating

Single Pulse Avalanche Capability

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



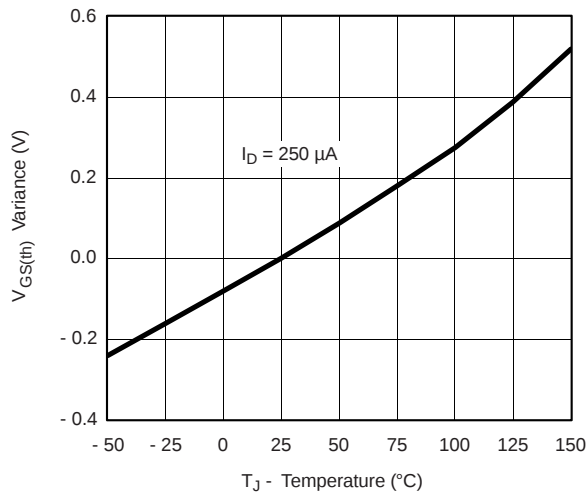
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



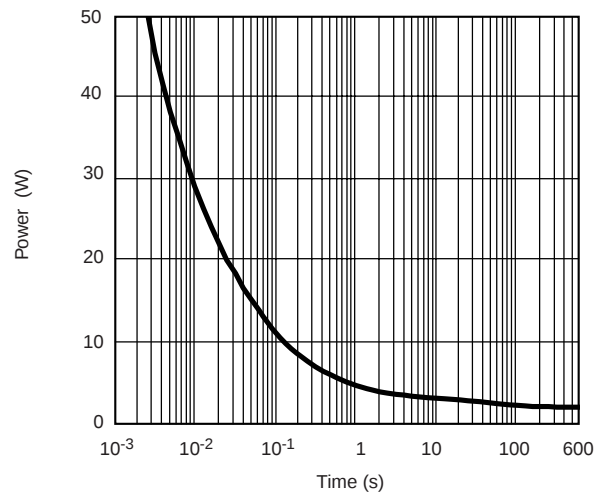
Source-Drain Diode Forward Voltage



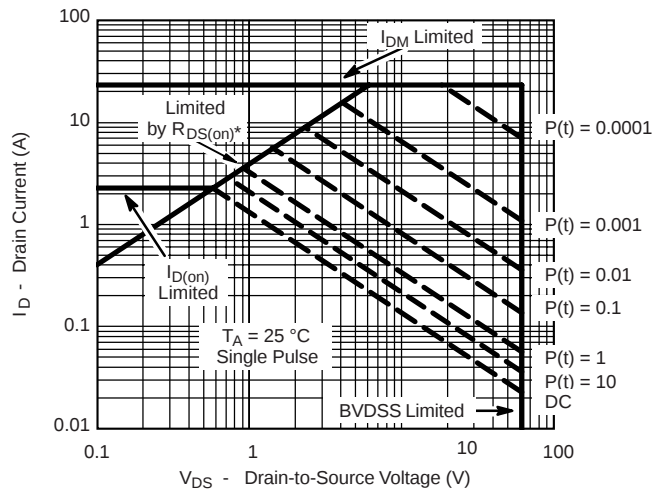
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



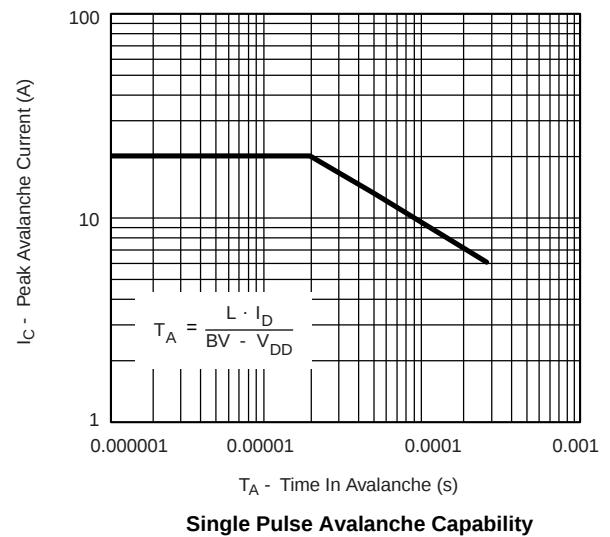
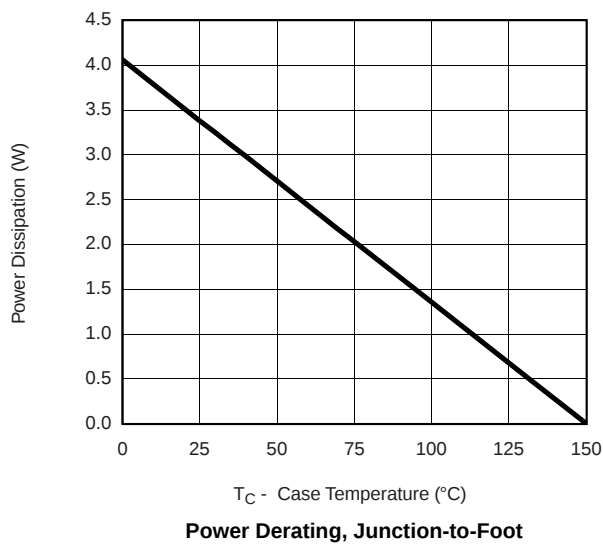
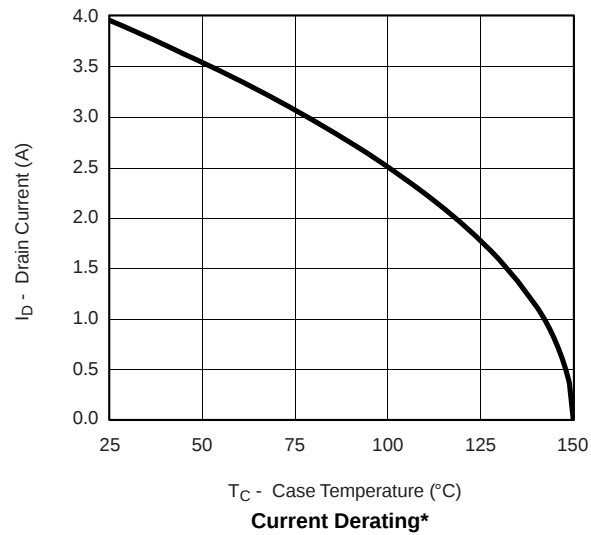
Single Pulse Power



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

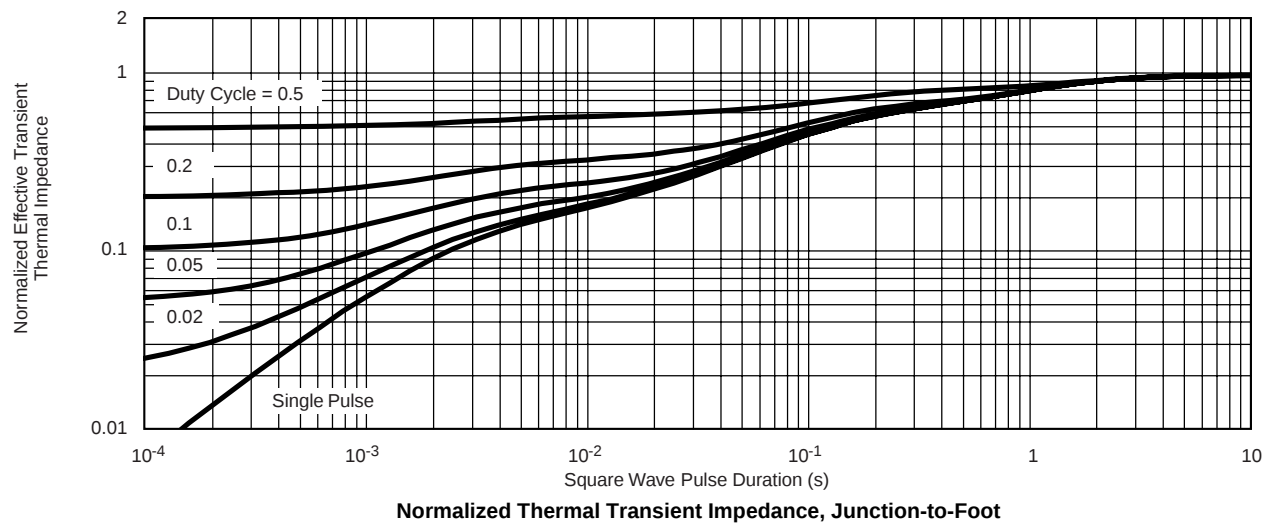
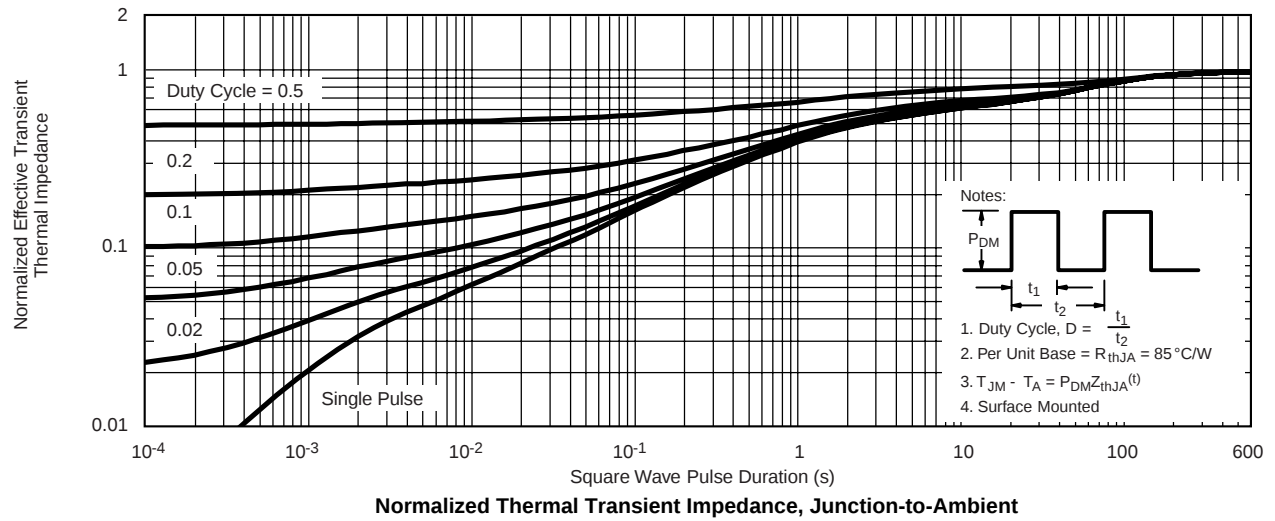
Safe Operating Area, Junction-to-Case

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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